

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

ECH8667— **General-Purpose Switching Device Applications**

Features

- ON-resistance RDS(on)1=30m Ω (typ.)
- · 4V drive
- · Halogen free compliance
- · Protection diode in

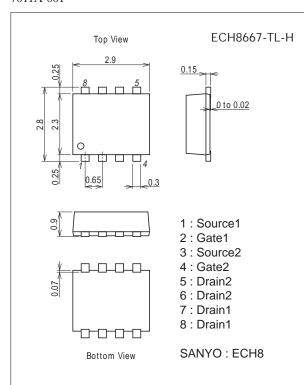
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-30	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	ID		-5.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-40	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	1.3	W
Total Dissipation	PT	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit: mm (typ) 7011A-001

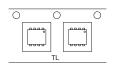


Product & Package Information

• Package : ECH8 • JEITA, JEDEC

• Minimum Packing Quantity : 3,000 pcs./reel

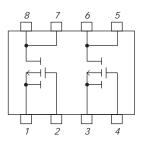
Packing Type: TL



Marking



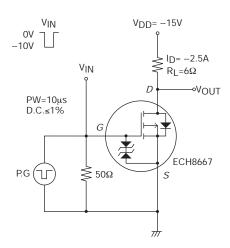
Electrical Connection



Electrical Characteristics at Ta=25°C

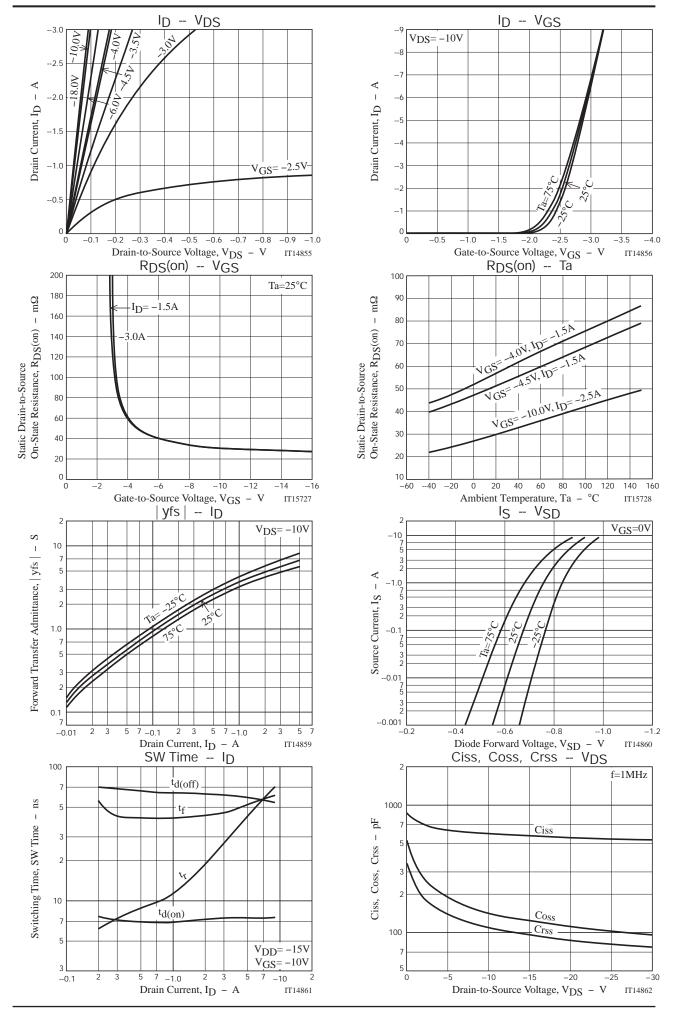
Parameter	Cumbal	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-30			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-30V, V _{GS} =0V			-1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V	
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-2.5A		5.2		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-2.5A, V _G S=-10V		30	39	mΩ	
	R _{DS} (on)2	I _D =-1.5A, V _G S=-4.5V		55	77	mΩ	
	R _{DS} (on)3	I _D =-1.5A, V _G S=-4V		58	82	mΩ	
Input Capacitance	Ciss			600		pF	
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz		145		pF	
Reverse Transfer Capacitance	Crss			110		pF	
Turn-ON Delay Time	t _d (on)			7.2		ns	
Rise Time	t _r	Constant Total Circuit		23		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		63		ns	
Fall Time	tf			42		ns	
Total Gate Charge	Qg			13		nC	
Gate-to-Source Charge	Qgs	V _{DS} =-15V, V _{GS} =-10V, I _D =-5.5A		1.8		nC	
Gate-to-Drain "Miller" Charge	Qgd			3.2		nC	
Diode Forward Voltage	V _{SD}	I _S =-5.5A, V _G S=0V		-0.82	-1.2	V	

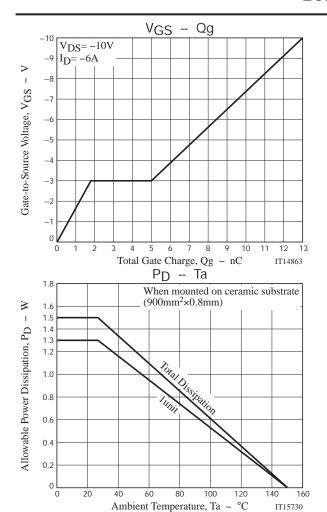
Switching Time Test Circuit

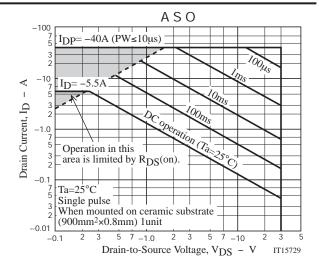


Ordering Information

Device	Package	Shipping	memo	
ECH8667-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free	





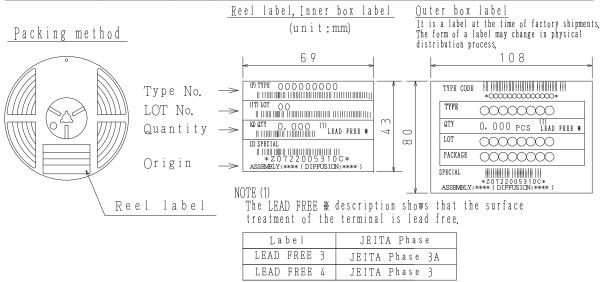


Embossed Taping Specification

ECH8667-TL-H

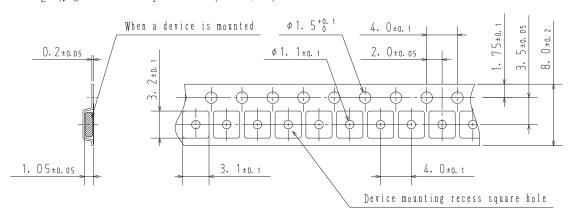
1. Packing Format

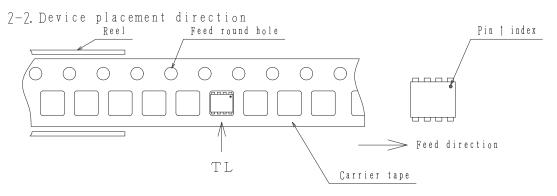
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	format
	Туре	Reel	Inner box	Outer box	Inner $BOX(C-1)$	Outer BOX (A-7)
ECH8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained
					Dimensions:mm (external)	Dimensions:mm (external)
					183×72×185	440×195×210



2. Taping configuration

2-1. Carrier tape size (unit:mm)

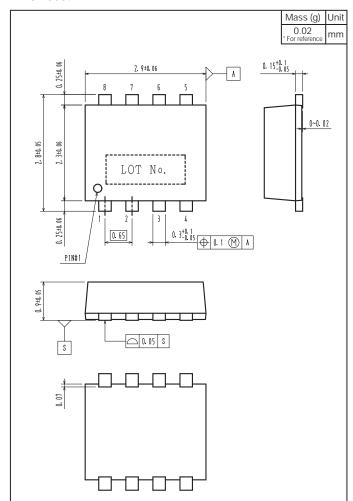




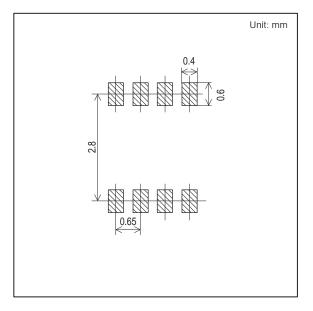
Those with pin 1 index on the feed hole side · · · · · TL

Outline Drawing

ECH8667-TL-H



Land Pattern Example



Note on usage: Since the ECH8667 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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